

#### **Description**

The VSM2312A uses advanced trench technology to provide excellent  $R_{\rm DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

•  $V_{DS} = 20V, I_D = 5A$ 

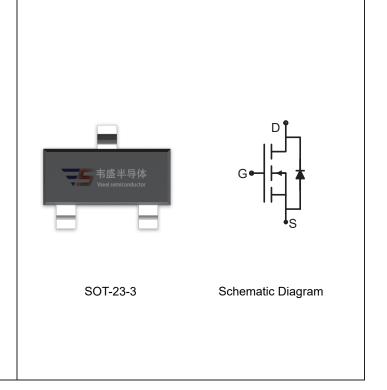
 $R_{DS(ON)}$  < 35m $\Omega$  @  $V_{GS}$ =2.5V

 $R_{DS(ON)}$  < 28m $\Omega$  @  $V_{GS}$ =4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

# **Application**

- Battery protection
- Load switch
- Power management



# Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM2312A-S2	VSM2312A	SOT-23-3	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

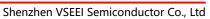
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	20	V	
Gate-Source Voltage	V <sub>G</sub> s	±10	V	
Drain Current-Continuous	I <sub>D</sub>	5	А	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	15	А	
Maximum Power Dissipation	P <sub>D</sub>	1.25	W	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$	

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	100	°C/W

## **Electrical Characteristics (T<sub>A</sub>=25℃ unless otherwise noted)**

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	22	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA	





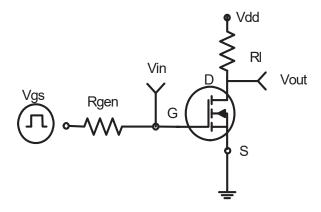
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.5	0.65	1.0	V
D : 0	R <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =4.5 A	-	20	35	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	17	28	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =15V,I <sub>D</sub> =5A	25	-	-	S
Dynamic Characteristics (Note4)	•					
Input Capacitance	C <sub>lss</sub>	)/ 40)/)/ 0)/	-	780	-	PF
Output Capacitance	Coss	$V_{DS}=10V, V_{GS}=0V,$	-	140	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	- F=1.0MHz	-	80	-	PF
Switching Characteristics (Note 4)	•					
Turn-on Delay Time	t <sub>d(on)</sub>		-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10V, $I_D$ =1A	-	30	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4.5 $V$ , $R_{GEN}$ =6 $\Omega$	-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	11	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =5A,V <sub>GS</sub> =4.5V	-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.9	-	nC
Drain-Source Diode Characteristics		•	•	•		•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5	Α

#### Notes:

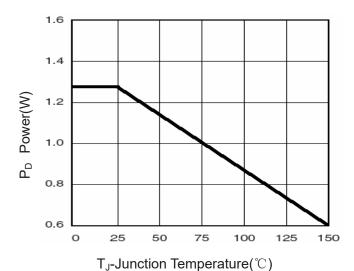
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- **4.** Guaranteed by design, not subject to production



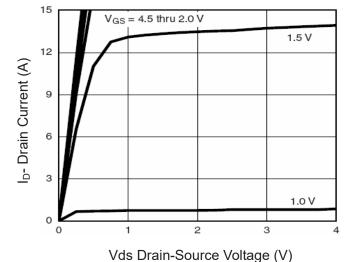
## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

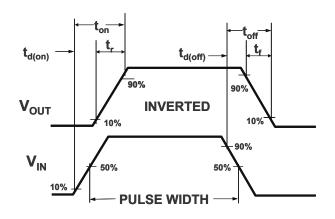
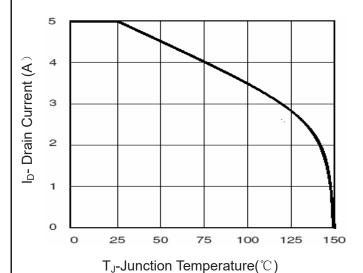


Figure 2:Switching Waveforms



**Figure 4 Drain Current** 

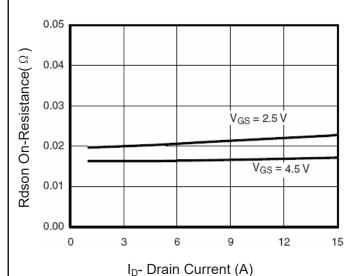
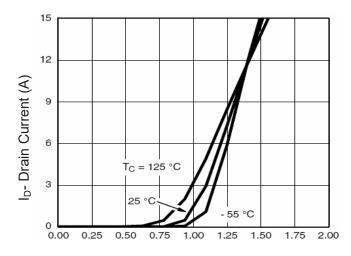


Figure 6 Drain-Source On-Resistance

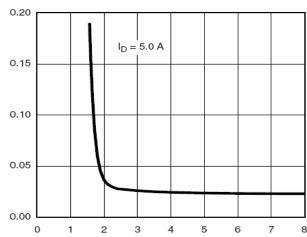


Rdson On-Resistance( (2)



Vgs Gate-Source Voltage (V)





Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

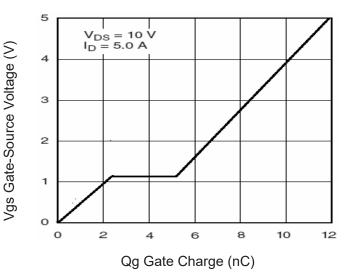


Figure 11 Gate Charge

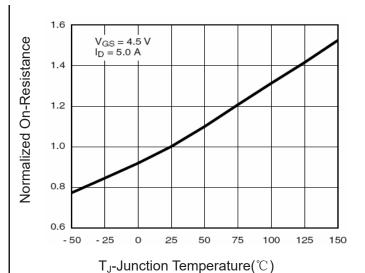


Figure 8 Drain-Source On-Resistance

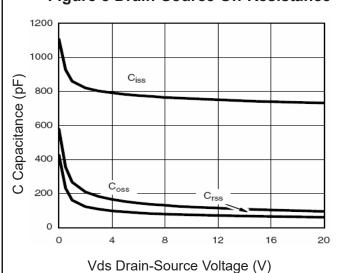


Figure 10 Capacitance vs Vds

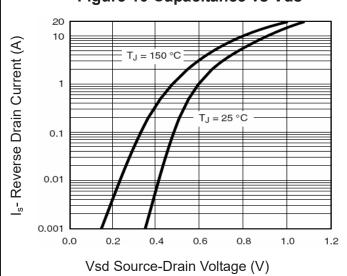
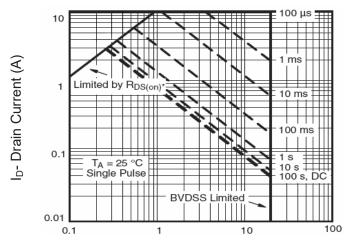


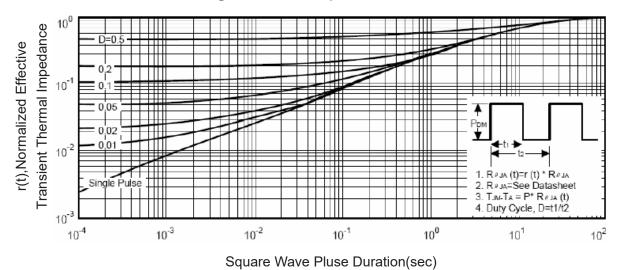
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance**